

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yoshihisa IWATA, et al.

SERIAL NO: New Application

GAU:

FILED: Herewith

EXAMINER:

FOR: MAGNETIC RANDOM ACCESS MEMORY DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☒ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
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CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
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C. Irvin McClelland
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Registration Number 21,124

LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent Number</u>	<u>Filing or Issue Date</u>	<u>Inventor/ Applicant</u>
237768US2S	10/438,015	05/15/03	IWATA et al.

DOCKET NO.: 248145US2S

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STATEMENT OF RELEVANCY

Reference AZ of Form PTO-1449:

This reference is mentioned in the specification.

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 248145US2S		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yoshihisa IWATA, et al.			
				FILING DATE Herewith		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	AA	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA	6,081,445	06/27/00	Jing SHI, et al.			
	AB	6,163,473	12/19/00	Lung T. TRAN			
	AC	6,205,051	03/20/01	James A. BRUG, et al.			
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AT	Roy SCHEUERLEIN, et al., "A 10ns Read and Write Non-Volatile Memory Array Using a Magnetic Tunnel Junction and FET Switch in each Cell", 2000 IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, ISSCC 2000, DIGEST OF TECHNICAL PAPERS, TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, Session 7, Paper TA 7.2, February 2000, 6 pages					
	AU	M. DURLAM, et al., "Nonvolatile RAM based on Magnetic Tunnel Junction Elements", 2000 IEEE INTERNATIONAL SOLID-STATE CIRCUITS CONFERENCE, ISSCC 2000, DIGEST OF TECHNICAL PAPERS, TD: EMERGING MEMORY & DEVICE TECHNOLOGIES, Session 7, Paper TA 7.3, February 2000, 6 pages					
	AV	Takeshi HONDA, et al., "MRAM-Writing Circuitry to Compensate for Thermal-Variation of Magnetization-Reversal Current", 2002 SYMPOSIUM ON VLSI CIRCUITS DIGEST OF TECHNICAL PAPERS, 12-3, June 2002, 2 pages					
	AW	M. MOTOYOSHI, et al., "High-Performance MRAM Technology with an Improved Magnetic Tunnel Junction Material", 2002 SYMPOSIUM ON VLSI DIGEST OF TECHNICAL PAPERS, 21.4, June 2002, Pages 212-213					
	AX	Manoj BHATTACHARYYA, et al., "Thermal Variations in Switching Fields for Sub-Micron MRAM Cells", IEEE TRANSACTIONS ON MAGNETICS, Vol. 37, No. 4, July 2001, Pages 1970-1972					
	AY	Ricardo C. SOUSA, et al., "Dynamic Switching of Tunnel Junction MRAM Cell with Nanosecond Field Pulses", IEEE TRANSACTIONS ON MAGNETICS, Vol. 36, No. 5, September 2000, Pages 2770-2772					
	AZ	Paul R. GRAY, et al., "Analysis and Design of Analog Integrated Circuits-2 nd Edition" Japanese Edition, 1 st Y. IWATA Volume, Pages 270-276				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							